

IN THE ABSTRACT OF THE DISCLOSURE

Page 50, lines 2-14, delete in their entirety and substitute therefore the following new Abstract of the Disclosure on the next page of this paper.

ABSTRACT OF THE DISCLOSURE

A memory cell of a magnetic memory includes a magnetoresistance element having free layer which includes ferromagnetic layers and a nonmagnetic film interposed therebetween, in which the magnetization directions of the ferromagnetic layers are equal to each other. The nonmagnetic film is a layer made of molybdenum having a thickness of 0.8 nm to 1.2 nm, a layer made of rhenium having a thickness of 1.4 nm to 1.8 nm, a layer made of tungsten having a thickness of 0.8 nm to 1.2 nm, a layer made of niobium having a thickness of 1.4 nm to 1.8 nm, a layer made of silicon having a thickness of 1.4 nm to 1.8 nm, a layer made of germanium having a thickness of 1.4 nm to 1.8 nm, a layer made of Al₂O₃ having a thickness of 1.0 nm, or a layer made of AlN having a thickness of 0.5 nm to 1.5 nm.